

ABSTRACT OF THE DISCLOSURE

WAKE-UP OF FERROELECTRIC THIN FILMS FOR PROBE STORAGE

A method for improving the stability of ferroelectric storage devices comprises: providing a ferroelectric storage medium including a film of ferroelectric material; and repeatedly applying a voltage to the film of ferroelectric material to improve the stability of polarized bits in the film of ferroelectric material. An apparatus that is used to perform the method is also provided.

FIGURE 3